

PC355NT

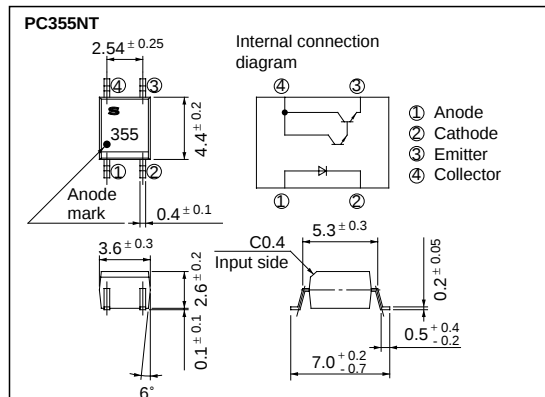
Mini-Flat Package, High Sensitivity Photocoupler

■ Features

1. High current transfer ratio
(CTR : MIN. 600% at $I_F = 1\text{mA}$, $V_{CE} = 2\text{V}$)
2. Opaque type, mini-flat package
PC355NT (1-channel)
3. Subminiature type
(The volume is smaller than that of our conventional DIP type by as far as 30%)
4. Isolation voltage between input and output
PC355NT••Viso : 3 750V_{rms}
5. Recognized by UL (NO. E64380)

■ Outline Dimensions

(Unit : mm)



■ Package Specifications

Model No.	Taping specifications
PC355NT	Taping reel diameter 178mm (750pcs.)

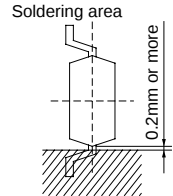
■ Applications

1. Hybrid substrates that require high density mounting.
2. Programmable controllers

Absolute Maximum Ratings

(Ta = 25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	*1 Peak forward current	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P	70	mW
Output	Collector-emitter voltage	V_{CEO}	35	V
	Emitter-collector voltage	V_{ECO}	6	V
	Collector current	I_C	80	mA
	Collector power dissipation	P_C	150	mW
Total power dissipation		P_{tot}	170	mW
*2 Isolation voltage		V_{iso}	3 750	V_{rms}
Operating temperature		T_{opr}	- 30 to + 100	°C
Storage temperature		T_{stg}	- 40 to + 125	°C
*3 Soldering temperature		T_{sol}	260	°C



*1 Pulse width ≤ 100 μs, Duty ratio : 0.001

*2 40 to 60% RH, AC for 1 minute

*3 For 10 seconds

Electro-optical Characteristics

(Ta = 25°C)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage		V_F	$I_F = 20\text{mA}$	-	1.2	1.4	V
	Reverse current		I_R	$V_R = 4\text{V}$	-	-	10	μ A
	Terminal capacitance		C_t	$V = 0, f = 1\text{kHz}$	-	30	250	pF
Output	Collector dark current		I_{CEO}	$V_{CE} = 10\text{V}, I_F = 0$	-	-	10^{-6}	A
	Collector-emitter breakdown voltage		BV_{CEO}	$I_C = 0.1\text{mA}, I_F = 0$	35	-	-	V
	Emitter-collector breakdown voltage		BV_{ECO}	$I_E = 10\text{μA}, I_F = 0$	6	-	-	V
Transfer-characteristics	Current transfer ratio		CTR	$I_F = 1\text{mA}, V_{CE} = 2\text{V}$	600	1 600	7 500	%
	Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_F = 20\text{mA}, I_C = 1\text{mA}$	-	0.8	1.0	V
	Isolation resistance		R_{ISO}	DC500V, 40 to 60% RH	5×10^{10}	10^{11}	-	Ω
	Floating capacitance		C_f	$V = 0, f = 1\text{MHz}$	-	0.6	1.0	pF
	Response time	Rise time	t_r	$V_{CE} = 2\text{V}, I_C = 2\text{mA}$ $R_L = 100\Omega$	-	60	300	μ s
		Fall time	t_f		-	53	250	μ s

Fig. 1 Forward Current vs. Ambient Temperature

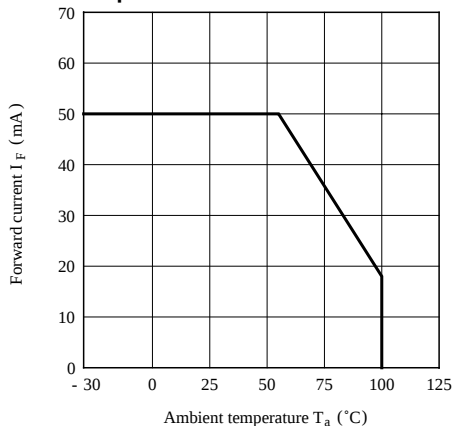


Fig. 2 Diode Power Dissipation vs. Ambient Temperature

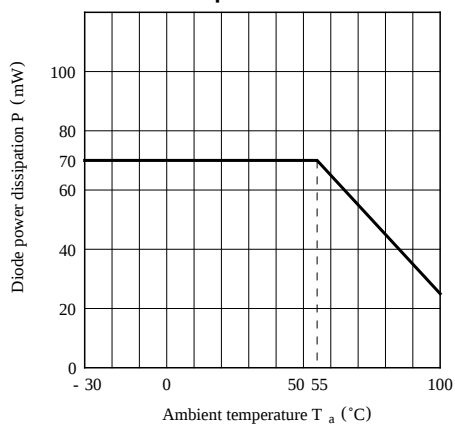


Fig. 3 Collector Power Dissipation vs. Ambient Temperature

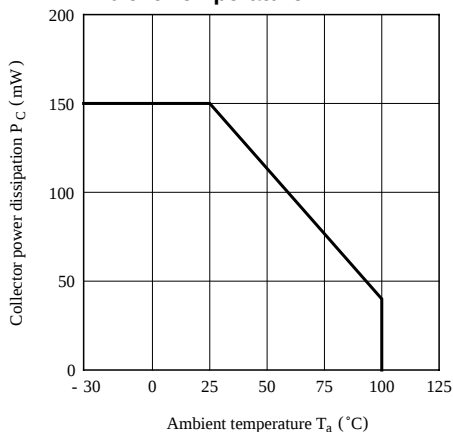


Fig. 4 Total Power Dissipation vs. Ambient Temperature

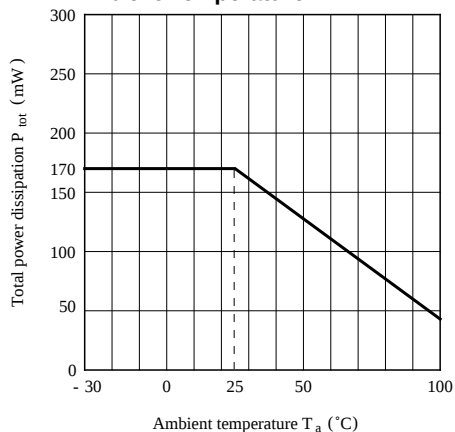


Fig. 5 Peak Forward Current vs. Duty Ratio

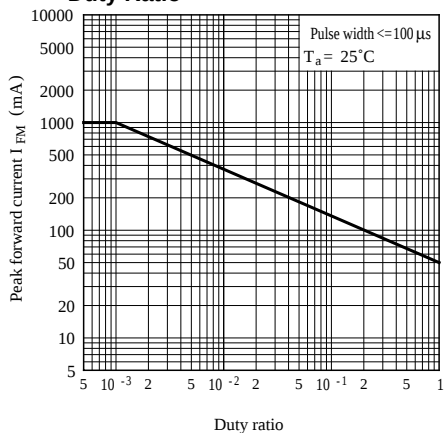


Fig. 6 Forward Current vs. Forward Voltage

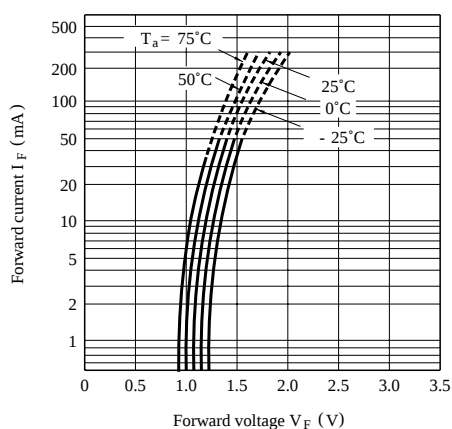


Fig. 7 Current Transfer Ratio vs. Forward Current

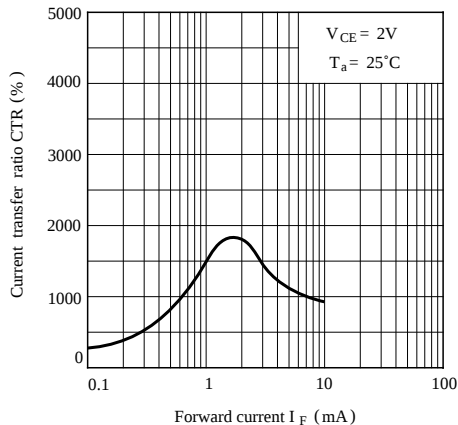


Fig. 8 Collector Current vs. Collector-emitter Voltage

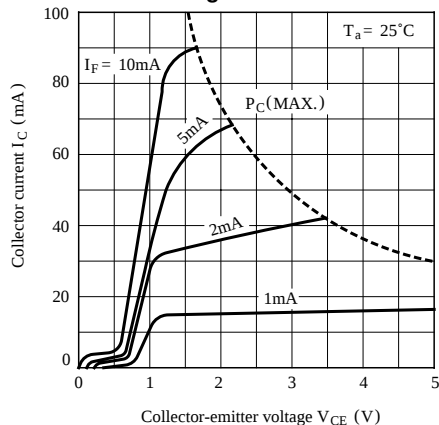


Fig. 9 Relative Current Transfer Ratio vs. Ambient Temperature

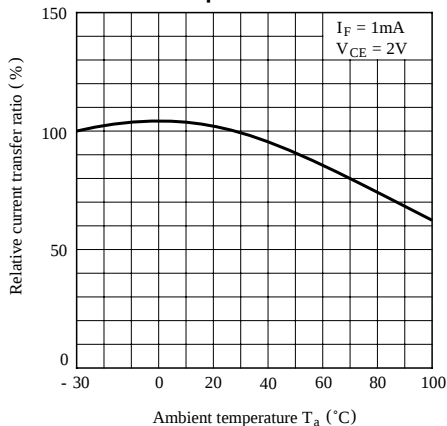


Fig.10 Collector-emitter Saturation Voltage vs. Ambient Temperature

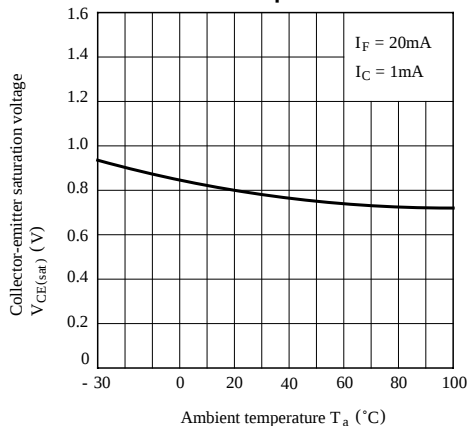


Fig.11 Collector Dark Current vs. Ambient Temperature

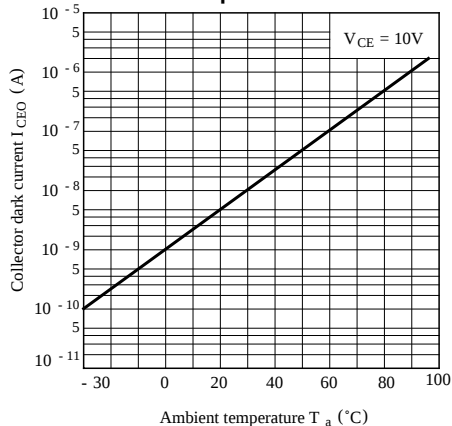
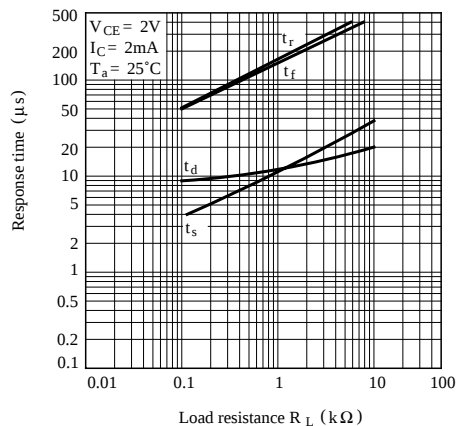


Fig.12 Responce Time vs. Load Resistance



Test Circuit For Response Time

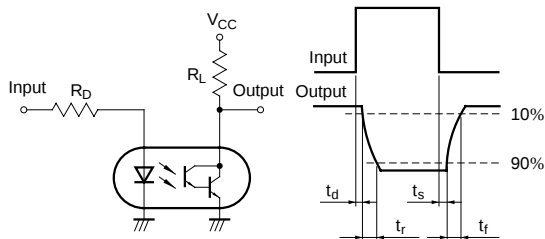
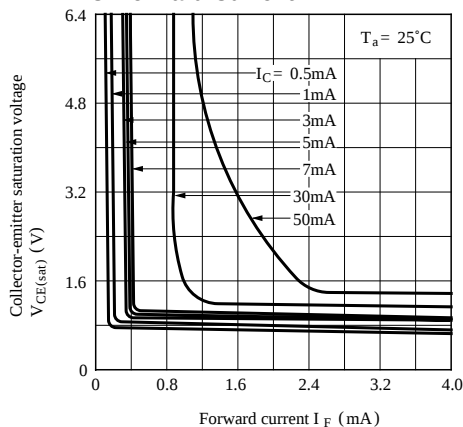
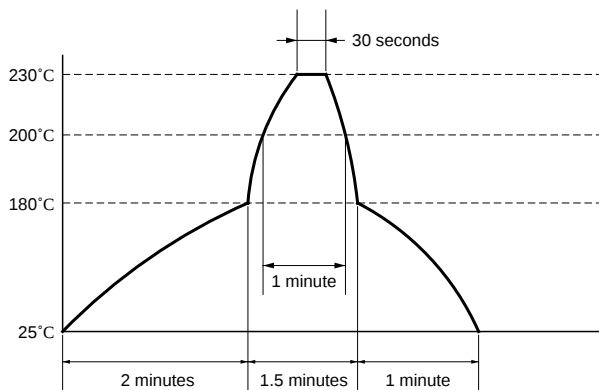


Fig.13 Collector-emitter Saturation Voltage vs. Forward Current



Temperature Profile of Soldering Reflow

- (1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.



- (2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.

Keep the temperature on the package of the device within the condition of above (1).

- Please refer to the chapter "Precautions for Use."